

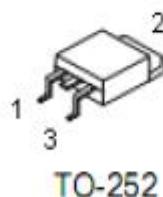
1. Features

- Advanced trench process technology
- High density cell design for ultra low on-resistance
- Fully characterized avalanche voltage and current

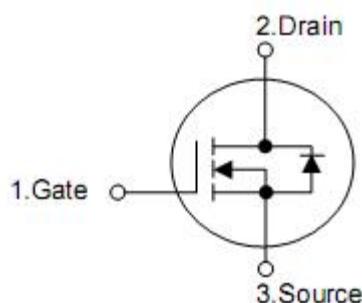
2. Features

- 50A, 30V, $R_{DS(on)}$ typ. = 6.5mΩ(typ.) @ $V_{GS} = 10$ V
- Low gate charge
- Low C_{rss}
- Fast switching
- Improved dv/dt capability

3. Pin configuration



TO-252



Pin	Function
1	Gate
2	Drain
3	Source

4. Ordering Information

Part Number	Package	Brand
KIA50N03BD	TO-252	KIA

5. Absolute maximum ratings

($T_C = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	30	V
I_D	Drain Current -Continuous ($T_C = 25^\circ\text{C}$)	50	A
	-Continuous ($T_C = 100^\circ\text{C}$)	30	A
I_{DM}	Drain Current -Pulsed	200	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy <small>(Note 1)</small>	85	mJ
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	60	W
	-Derate above 25°C	0.5	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

6. Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.8	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	$^\circ\text{C}/\text{W}$

7. Electrical characteristics

($T_C = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
B_{VDSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	--	--	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	--	--	1	μA
I_{GSS}	Gate- Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	--	--	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1.0	1.6	3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	--	6.5	9.9	$\text{m}\Omega$
R_G	Gate Resistance	$f = 1.0 \text{ MHz}$	--	5.0	--	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	--	1200	--	pF
C_{oss}	Output Capacitance		--	150	--	pF
C_{rss}	Reverse Transfer Capacitance		--	115	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 20 \text{ V}, V_{GS}=10\text{V}, I_D = 15 \text{ A}, R_G = 6 \Omega$ (Note 2,3)	--	4.6	--	ns
t_r	Turn-On Rise Time		--	35	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	40	--	ns
t_f	Turn-Off Fall Time		--	16	--	ns
Q_g	Total Gate Charge	$V_{DD} = 24 \text{ V}, I_D = 15\text{A}, V_{GS} = 10 \text{ V}$ (Note 2,3)	--	25	--	nC
Q_{gs}	Gate-Source Charge		--	5.0	--	nC
Q_{gd}	Gate-Drain Charge		--	5.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_s	Continuous Source Current	Integral Reverse P-N Junction Diode in the MOSFET	--	--	50	A
I_{SM}	Pulsed Source Current		--	--	200	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_s = 15 \text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_s = 15 \text{ A}, dI_F / dt = 100 \text{ A/us}$ (Note 2)	--	12.5	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.005	--	uC

Notes:

1. $L = 0.5\text{mH}, V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

2. Pulse Test : Pulse width $\leq 300\text{us}$, Duty cycle $\leq 2\%$

3. Essentially independent of operating temperature

8. Typical Characteristics

Figure 1. Output Characteristics

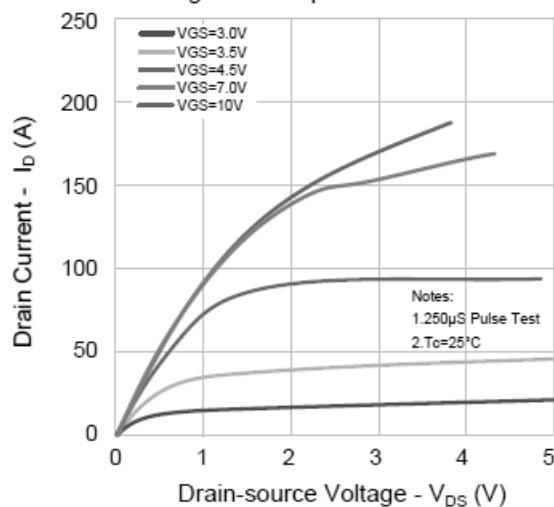


Figure 3. On-resistance vs. Drain Current

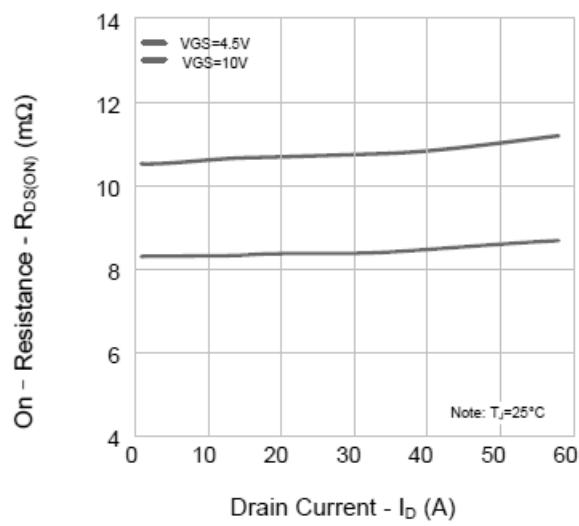


Figure 5. Capacitance Characteristics

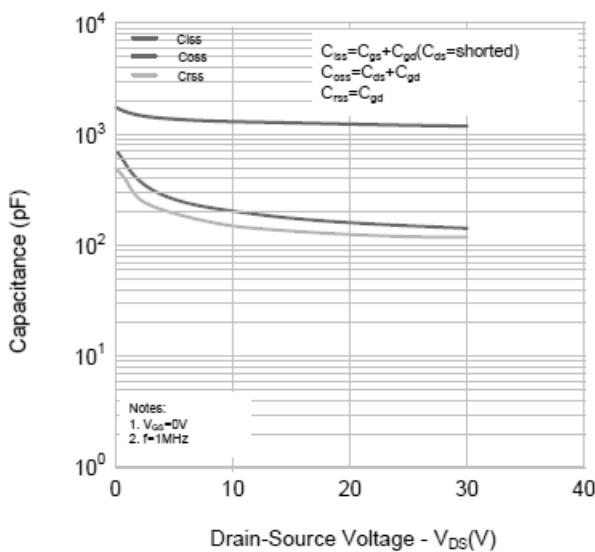


Figure 2. Transfer Characteristics

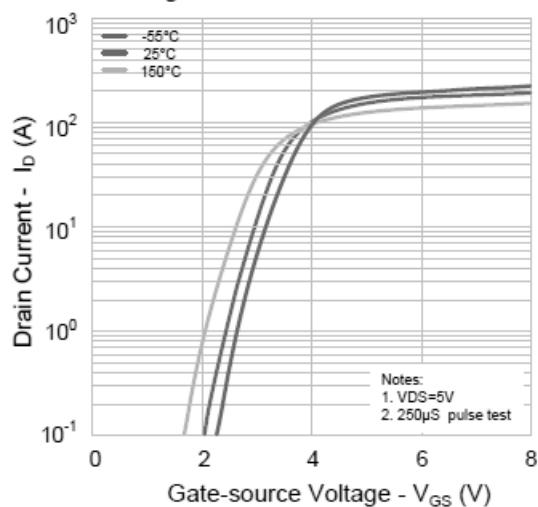


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

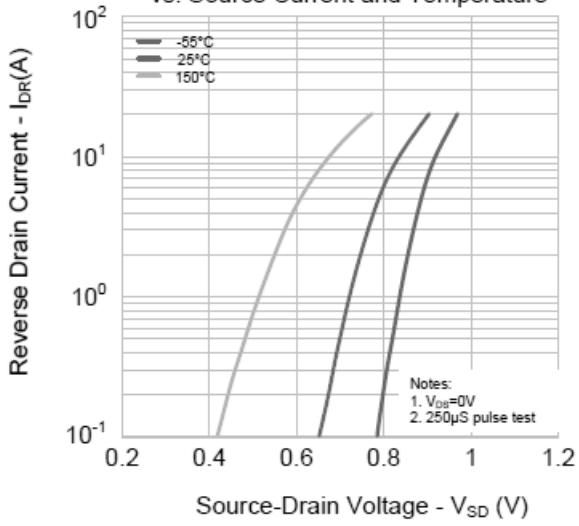
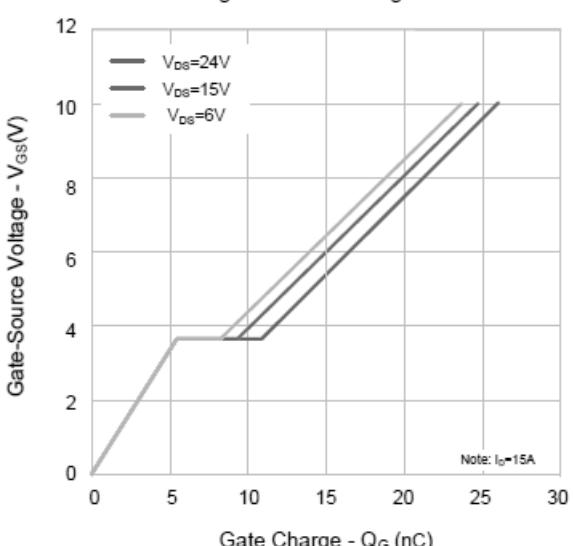


Figure 6. Gate Charge



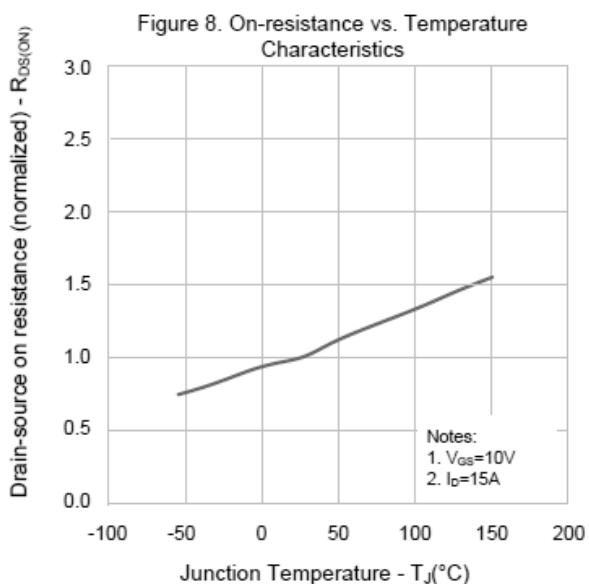
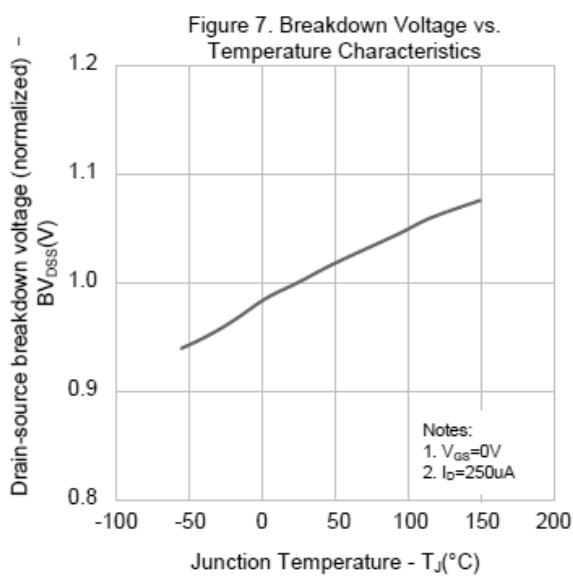
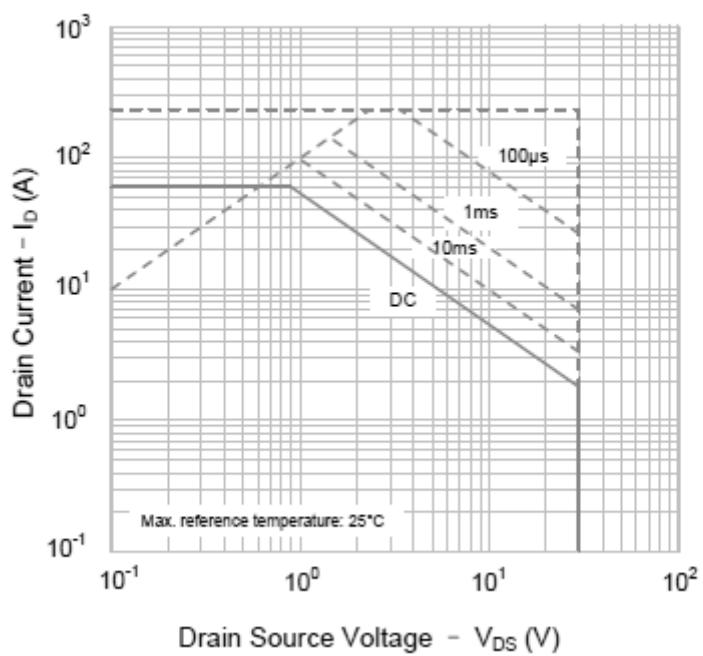


Figure 9. Max. Safe Operating Area



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